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Kind regards,

Team Nexperia

74LV00Quad 2-input NAND gate Rev. 4 — 9 December 2015

Product data sheet

1. **General description**

The 74LV00 is a low-voltage Si-gate CMOS device that is pin and function compatible with 74HC00 and 74HCT00.

The 74LV00 provides a quad 2-input NAND function.

Features and benefits 2.

- Wide operating voltage: 1.0 V to 5.5 V
- Optimized for low voltage applications: 1.0 V to 3.6 V
- Accepts TTL input levels between V_{CC} = 2.7 V and V_{CC} = 3.6 V
- Typical output ground bounce < 0.8 V at V_{CC} = 3.3 V and T_{amb} = 25 °C
- Typical HIGH-level output voltage (V_{OH}) undershoot: > 2 V at V_{CC} = 3.3 V and $T_{amb} = 25 \, ^{\circ}C$
- ESD protection:
 - ◆ HBM JESD22-A114F exceeds 2000 V
 - ◆ MM JESD22-A115-A exceeds 200 V
- Multiple package options
- Specified from -40 °C to +85 °C and from -40 °C to +125 °C

Ordering information

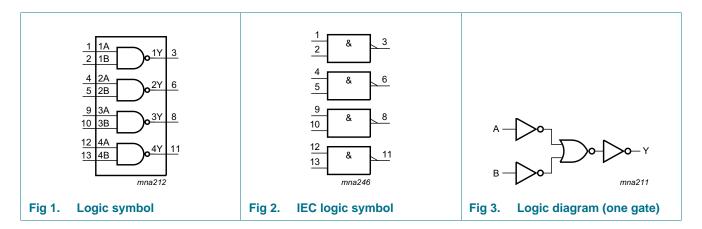
Table 1. **Ordering information**

Type number	Package										
	Temperature range	Name	Description	Version							
74LV00D	–40 °C to +125 °C	SO14	plastic small outline package; 14 leads; body width 3.9 mm	SOT108-1							
74LV00DB	–40 °C to +125 °C	SSOP14	plastic shrink small outline package; 14 leads; body width 5.3 mm	SOT337-1							
74LV00PW	–40 °C to +125 °C	TSSOP14	plastic thin shrink small outline package; 14 leads; body width 4.4 mm	SOT402-1							
74LV00BQ	-40 °C to +125 °C	DHVQFN14	plastic dual in-line compatible thermal enhanced very thin quad flat package; no leads; 14 terminals; body $2.5 \times 3 \times 0.85$ mm	SOT762-1							



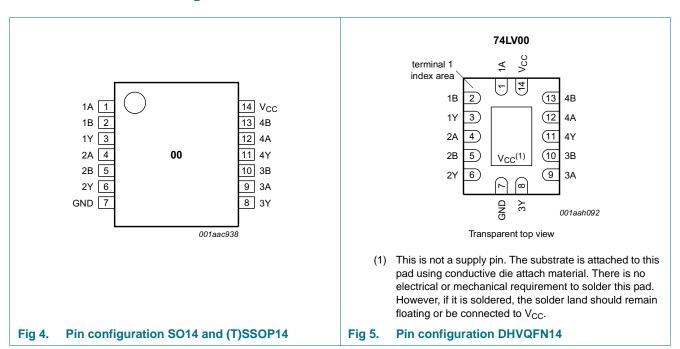
Quad 2-input NAND gate

4. Functional diagram



5. Pinning information

5.1 Pinning



Quad 2-input NAND gate

5.2 Pin description

Table 2. Pin description

Symbol	Pin	Description
1A to 4A	1, 4, 9, 12	data input
1B to 4B	2, 5, 10, 13	data input
1Y to 4Y	3, 6, 8, 11	data output
GND	7	ground (0 V)
V _{CC}	14	supply voltage

6. Functional description

Table 3. Function table[1]

Input							
nA	nB	nY					
L	X	Н					
X	L	Н					
Н	Н	L					

^[1] H = HIGH voltage level; L = LOW voltage level; X = don't care

7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{CC}	supply voltage			-0.5	+7.0	V
I _{IK}	input clamping current	$V_{I} < -0.5 \text{ V or } V_{I} > V_{CC} + 0.5 \text{ V}$	<u>[1]</u>	-	±20	mA
I _{OK}	output clamping current	V_{O} < -0.5 V or V_{O} > V_{CC} + 0.5 V	<u>[1]</u>	-	±50	mA
Io	output current	$V_{O} = -0.5 \text{ V to } (V_{CC} + 0.5 \text{ V})$		-	±25	mA
I _{CC}	supply current			-	50	mA
I _{GND}	ground current			-50	-	mA
T _{stg}	storage temperature			–65	+150	°C
P _{tot}	total power dissipation	$T_{amb} = -40 ^{\circ}\text{C} \text{ to } +125 ^{\circ}\text{C}$				
		SO14 package	[2]	-	500	mW
		(T)SSOP14 package	[3]	-	500	mW
		DHVQFN14 package	[4]	-	500	mW

^[1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

^[2] P_{tot} derates linearly with 8 mW/K above 70 °C.

^[3] Ptot derates linearly with 5.5 mW/K above 60 °C.

^[4] Ptot derates linearly with 4.5 mW/K above 60 °C.

Quad 2-input NAND gate

8. Recommended operating conditions

Table 5. Recommended operating conditions

Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{CC}	supply voltage	[1]	1.0	3.3	5.5	V
VI	input voltage		0	-	V _{CC}	V
Vo	output voltage		0	-	V _{CC}	V
T _{amb}	ambient temperature		-40	+25	+125	°C
Δt/ΔV	input transition rise and fall rate	V _{CC} = 1.0 V to 2.0 V	-	-	500	ns/V
		$V_{CC} = 2.0 \text{ V to } 2.7 \text{ V}$	-	-	200	ns/V
		$V_{CC} = 2.7 \text{ V to } 3.6 \text{ V}$	-	-	100	ns/V
		$V_{CC} = 3.6 \text{ V to } 5.5 \text{ V}$	-	-	50	ns/V

^[1] The static characteristics are guaranteed from V_{CC} = 1.2 V to V_{CC} = 5.5 V, but LV devices are guaranteed to function down to V_{CC} = 1.0 V (with input levels GND or V_{CC}).

9. Static characteristics

Table 6. Static characteristics

Voltages are referenced to GND (ground = 0 V).

Symbol V _{IH}	Parameter	Conditions	-40	°C to +8	85 °C	-40 °C to	Unit	
			Min	Typ[1]	Max	Min	Max	
V _{IH}	HIGH-level input voltage	V _{CC} = 1.2 V	0.9	-	-	0.9	-	V
		V _{CC} = 2.0 V	1.4	-	-	1.4	-	V
		$V_{CC} = 2.7 \text{ V to } 3.6 \text{ V}$	2.0	-	-	2.0	-	V
		V _{CC} = 4.5 V to 5.5 V	0.7V _{CC}	-	-	0.7V _{CC}	- V - V - V 0.3 V 0.6 V 0.8 V 0.3V _{CC} V - V - V - V - V - V	
V _{IL}	LOW-level input voltage	V _{CC} = 1.2 V	-	-	0.3	-	0.3	V
		V _{CC} = 2.0 V	-	-	0.6	-	0.6	V
		$V_{CC} = 2.7 \text{ V to } 3.6 \text{ V}$	-	-	0.8	-	0.8	V
		V _{CC} = 4.5 V to 5.5 V	-	-	0.3V _{CC}	-	0.3V _{CC}	V
V _{OH}	HIGH-level output voltage	$V_I = V_{IH}$ or V_{IL}						
		$I_O = -100 \mu A; V_{CC} = 1.2 V$	-	1.2	-	-	-	V
		$I_O = -100 \mu A; V_{CC} = 2.0 V$	1.8		1.8	-	V	
		$I_{O} = -100 \mu A; V_{CC} = 2.7 V$	2.5	2.7	-	2.5	-	V
		$I_O = -100 \mu A; V_{CC} = 3.0 V$	2.8	3.0	-	2.8	-	V
		$I_O = -100 \mu A; V_{CC} = 4.5 V$	4.3	4.5	-	4.3	-	V
		$I_O = -6 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.4	2.82	-	2.2	-	V
V _{OH} F		$I_O = -12 \text{ mA}; V_{CC} = 4.5 \text{ V}$	3.6	4.2	-	3.5	-	V

Table 6. Static characteristics ...continued Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	-40	°C to +8	85 °C	-40 °C to	+125 °C	Unit
			Min	Typ[1]	Max	Min	Max	
V_{OL}	LOW-level output voltage	$V_I = V_{IH}$ or V_{IL}						
		$I_O = 100 \mu A; V_{CC} = 1.2 V$	-	0	-	-	-	V
		$I_O = 100 \mu A; V_{CC} = 2.0 \text{ V}$	-	0	0.2	-	0.2	V
		$I_O = 100 \mu A; V_{CC} = 2.7 V$	-	0	0.2	-	0.2	V
		$I_O = 100 \mu A; V_{CC} = 3.0 \text{ V}$	-	0	0.2	-	0.2	V
		$I_O = 100 \mu A; V_{CC} = 4.5 V$	-	0	0.2	-	0.2	V
		$I_O = 6 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	0.25	0.40	-	0.50	V
		$I_{O} = 12 \text{ mA}; V_{CC} = 4.5 \text{ V}$	-	0.35	0.55	-	0.65	V
I _I	input leakage current	$V_I = V_{CC}$ or GND; $V_{CC} = 5.5 \text{ V}$	-	-	1.0	-	1.0	μΑ
I _{CC}	supply current	$V_I = V_{CC}$ or GND; $I_O = 0$ A; $V_{CC} = 5.5 \text{ V}$	-	-	20.0	-	40	μΑ
Δl _{CC}	additional supply current	per input; $V_I = V_{CC} - 0.6 \text{ V}$; $V_{CC} = 2.7 \text{ V}$ to 3.6 V	-	-	500	-	850	μΑ
Cı	input capacitance		-	3.5	-	-	-	pF

^[1] Typical values are measured at T_{amb} = 25 °C.

10. Dynamic characteristics

Table 7. Dynamic characteristics GND = 0 *V; For test circuit see Figure 7.*

Symbol	Parameter	Conditions		-40	°C to +85	S °C	–40 °C t	o +125 °C	Unit
				Min	Typ[1]	Max	Min	Max	
t _{pd}	propagation delay	nA, nB to nY; see Figure 6	[2]						
		V _{CC} = 1.2 V		-	45	-	-	-	ns
		V _{CC} = 2.0 V		-	15	26	-	31	ns
		V _{CC} = 2.7 V		-	11	18	-	23	ns
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V; } C_L = 15 \text{ pF}$	[3]	-	7	-	-	-	ns
		V _{CC} = 3.0 V to 3.6 V	[3]	-	9.0	15	-	18	ns
		V _{CC} = 4.5 V to 5.5 V	[3]	-	6.5	11	-	14	ns
C _{PD}	power dissipation capacitance	C_L = 50 pF; f_i = 1 MHz; V_I = GND to V_{CC}	[4]	-	22	-	-	-	pF

- [1] All typical values are measured at T_{amb} = 25 °C.
- [2] t_{pd} is the same as t_{PLH} and t_{PHL} .
- [3] Typical values are measured at nominal supply voltage (V_{CC} = 3.3 V and V_{CC} = 5.0 V).
- [4] C_{PD} is used to determine the dynamic power dissipation (P_D in μW).

 $P_D = C_{PD} \times V_{CC}{}^2 \times f_i \times N + \Sigma (C_L \times V_{CC}{}^2 \times f_o) \text{ where:}$

 f_i = input frequency in MHz, f_o = output frequency in MHz

C_L = output load capacitance in pF

 V_{CC} = supply voltage in V

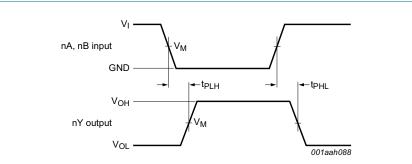
N = number of inputs switching

 $\Sigma(C_L \times V_{CC}^2 \times f_o)$ = sum of the outputs.

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Quad 2-input NAND gate

11. Waveforms



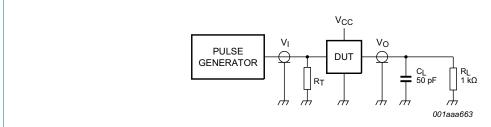
Measurement points are given in Table 8.

 V_{OL} and V_{OH} are typical voltage output levels that occur with the output load.

Fig 6. The input (nA, nB) to output (nY) propagation delays

Table 8. Measurement points

Supply voltage	Input	Output
Vcc	V _M	V _M
< 2.7 V	0.5V _{CC}	0.5V _{CC}
2.7 V to 3.6 V	1.5 V	1.5 V
≥ 4.5 V	0.5V _{CC}	0.5V _{CC}



Test data is given in Table 9.

Definitions test circuit:

 R_T = Termination resistance should be equal to output impedance Z_0 of the pulse generator.

 R_L = Load resistance.

 C_L = Load capacitance including jig and probe capacitance.

Fig 7. Test circuit for measuring switching times

Table 9. Test data

Supply voltage	Input				
V _{CC}	V _I	t _r , t _f			
< 2.7 V	V _{CC}	≤ 2.5 ns			
2.7 V to 3.6 V	2.7 V	≤ 2.5 ns			
≥ 4.5 V	V _{CC}	≤ 2.5 ns			

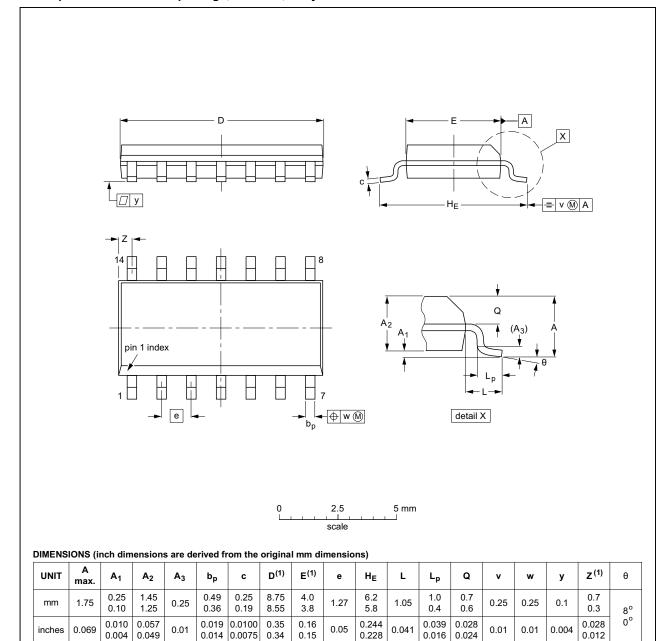
74LV00

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12. Package outline

SO14: plastic small outline package; 14 leads; body width 3.9 mm

SOT108-1



Note

1. Plastic or metal protrusions of 0.15 mm (0.006 inch) maximum per side are not included.

OUTLINE		REFER	EUROPEAN	ISSUE DATE		
VERSION	IEC	JEDEC	JEITA	PROJECTION	135UE DATE	
SOT108-1	076E06	MS-012			99-12-27 03-02-19	

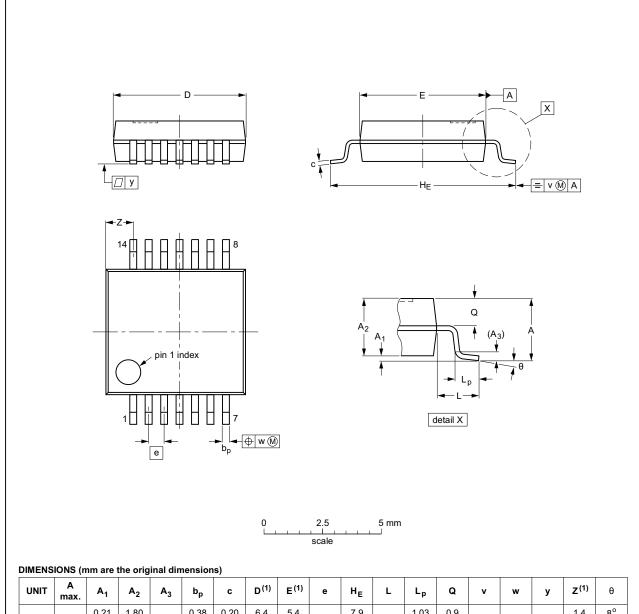
Fig 8. Package outline SOT108-1 (SO14)

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SSOP14: plastic shrink small outline package; 14 leads; body width 5.3 mm

SOT337-1



UNIT	A max.	A ₁	A ₂	A ₃	b _p	C	D ⁽¹⁾	E ⁽¹⁾	е	HE	L	Lp	Q	v	w	у	Z ⁽¹⁾	θ
mm	2	0.21 0.05	1.80 1.65	0.25	0.38 0.25	0.20 0.09	6.4 6.0	5.4 5.2	0.65	7.9 7.6	1.25	1.03 0.63	0.9 0.7	0.2	0.13	0.1	1.4 0.9	8° 0°

Note

1. Plastic or metal protrusions of 0.25 mm maximum per side are not included.

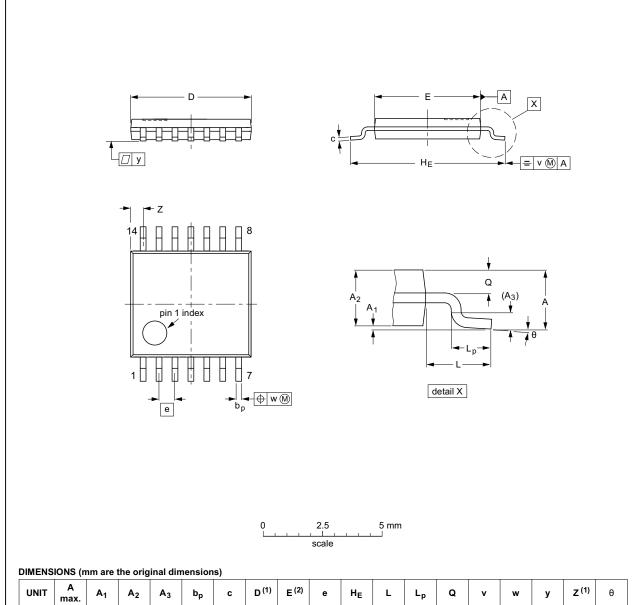
OUTLINE		REFER	EUROPEAN	ISSUE DATE		
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE
SOT337-1		MO-150				99-12-27 03-02-19

Package outline SOT337-1 (SSOP14) Fig 9.

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TSSOP14: plastic thin shrink small outline package; 14 leads; body width 4.4 mm

SOT402-1



UNIT	A max.	A ₁	A ₂	A ₃	bp	C	D ⁽¹⁾	E ⁽²⁾	е	HE	L	Lp	Q	>	w	у	Z ⁽¹⁾	θ
mm	1.1	0.15 0.05	0.95 0.80	0.25	0.30 0.19	0.2 0.1	5.1 4.9	4.5 4.3	0.65	6.6 6.2	1	0.75 0.50	0.4 0.3	0.2	0.13	0.1	0.72 0.38	8° 0°

Notes

- 1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.
- 2. Plastic interlead protrusions of 0.25 mm maximum per side are not included.

		EUROPEAN	ISSUE DATE		
ION IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE
02-1	MO-153				99-12-27 03-02-18
_	IEC	IEC JEDEC	IEC JEDEC JEHA	IEC JEDEC JEHA	NO 450

Fig 10. Package outline SOT402-1 (TSSOP14)

74LV00

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DHVQFN14: plastic dual in-line compatible thermal enhanced very thin quad flat package; no leads; 14 terminals; body $2.5 \times 3 \times 0.85$ mm

SOT762-1

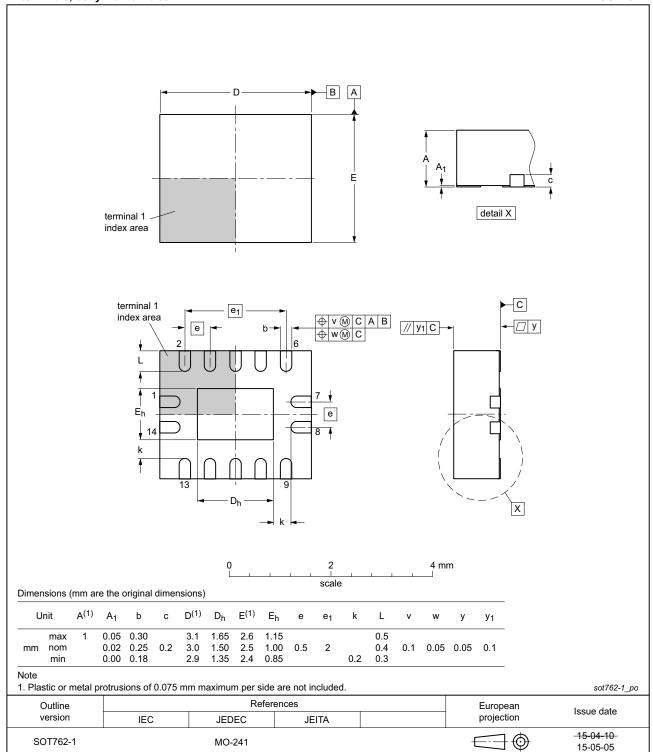


Fig 11. Package outline SOT762-1 (DHVQFN14)

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Quad 2-input NAND gate

13. Abbreviations

Table 10. Abbreviations

Acronym	Description
CMOS	Complementary Metal Oxide Semiconductor
DUT	Device Under Test
ESD	ElectroStatic Discharge
НВМ	Human Body Model
MM	Machine Model
TTL	Transistor-Transistor Logic

14. Revision history

Table 11. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes					
74LV00 v.4	20151209	Product data sheet	-	74LV00 v.3					
Modifications:	Type number 74LV00N (SOT27-1) removed.								
74LV00 v.3	20071220	Product data sheet	-	74LV00 v.2					
Modifications:	 The format of this data sheet has been redesigned to comply with the new identity guidelines of NXP Semiconductors. 								
	 Legal texts have been adapted to the new company name where appropriate. 								
	Section 3: DHVQFN14 package added.								
	 Section 7: derating values added for DHVQFN14 package. 								
	 <u>Section 12</u>: outline drawing added for DHVQFN14 package. 								
74LV00 v.2	19980420	Product specification	-	74LV00 v.1					
74LV00 v.1	19970203	Product specification	-	-					

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15. Legal information

15.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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Product [short] data sheet	Production	This document contains the product specification.

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Please be aware that important notices concerning this document and the product(s) described herein, have been included in section 'Legal information'.